

## Silicon Epitaxial Planar Diode

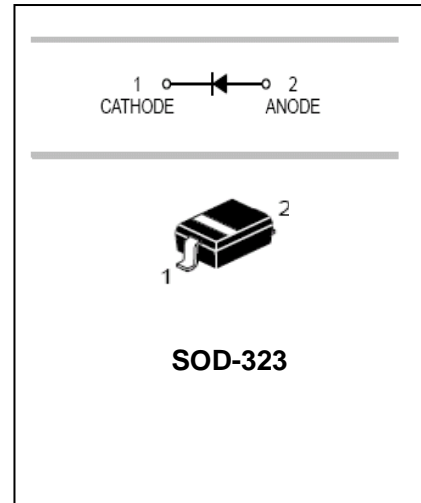
## 1SS355

### FEATURES

- Small Surface Mounting Type:  
SOD-323
- High Speed :t=1.2ns Typ.
- High Reliability With High Surge Current Handling Capability.



Lead-free



### APPLICATIONS

- High speed switching

### ORDERING INFORMATION

Type No.	Marking	Package Code
1SS355	A	SOD-323

### MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	$V_{RM}$	90	V
DC Reverse Voltage	$V_R$	80	V
Peak forward Current	$I_{FM}$	225	mA
Average Rectified Output Current	$I_O$	100	mA
Surge current (1s)	$I_{surge}$	500	mA
Power Dissipation	$P_D$	200	mW
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{STG}$	-55~+125	°C

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### ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$			1.2	V	$I_F=100\text{mA}$
Reverse current	$I_R$			0.1	$\mu\text{A}$	$V_R=80\text{V}$
Capacitance between terminals	$C_T$			3	pF	$V_R=0.5\text{V}, f=1\text{MHz}$
Reverse Recovery Time	$t_{rr}$			4	ns	$I_F=10\text{mA}, V_R=6\text{V}, R_L=100\Omega$

### TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

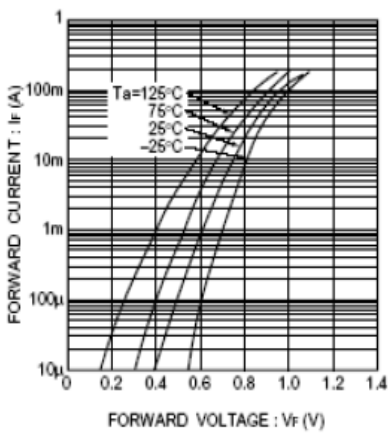


Fig.1 Forward characteristics

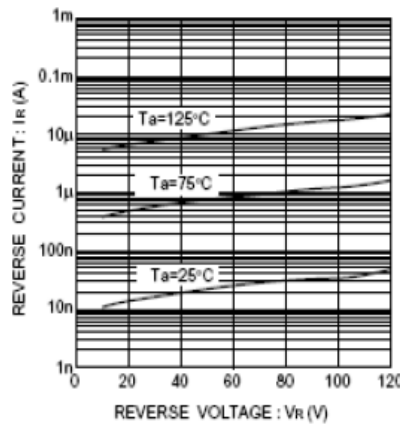


Fig.2 Reverse characteristics

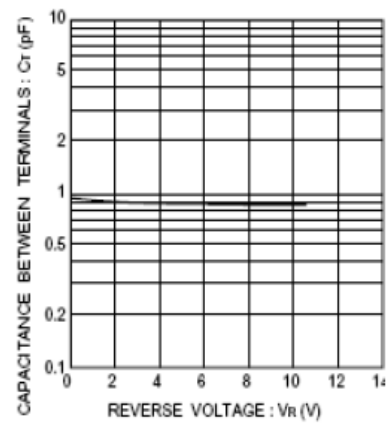


Fig.3 Capacitance between terminals characteristics

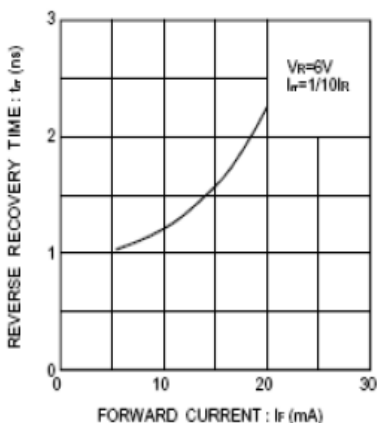


Fig.4 Reverse recovery time characteristics

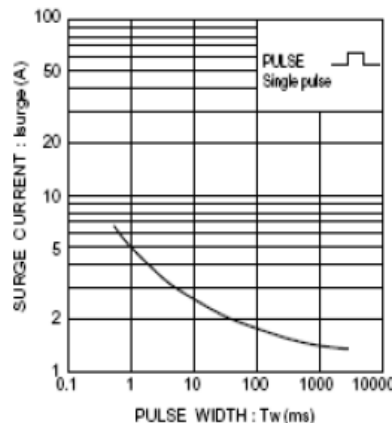


Fig.5 Surge current characteristics

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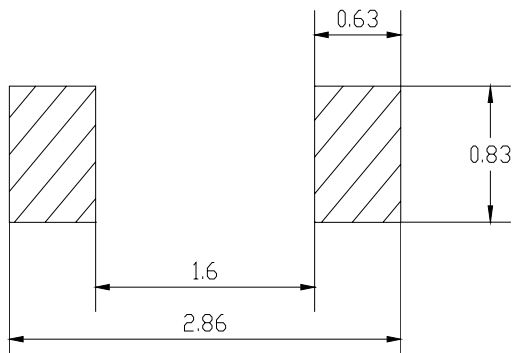
### PACKAGE OUTLINE

Plastic surface mounted package

SOD-323

SOD-323		
Dim	Min	Max
A	1.275	1.325
B	1.675	1.725
C	0.9 Typical	
D	0.25	0.35
E	0.27	0.37
H	0.02	0.1
J	0.1 Typical	
K	2.6	2.7
All Dimensions in mm		

### SOLDERING FOOTPRINT



Unit : mm

### PACKAGE INFORMATION

Device	Package	Shipping
1SS355	SOD-323	3000/Tape&Reel